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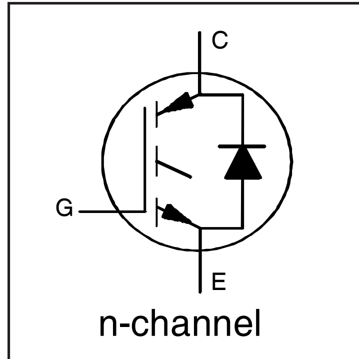
International
IOR Rectifier

IRGPS4067DPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE



V_{CES} = 600V

$I_{C(Nominal)}$ = 120A

$t_{SC} \geq$ 5µs, $T_{J(max)}$ = 175°C

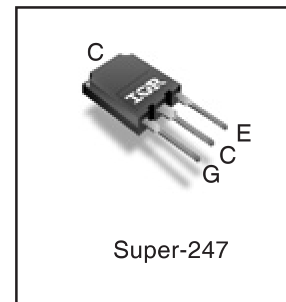
$V_{CE(on)}$ typ. = 1.70V

Features

- Low $V_{CE\ (on)}$ Trench IGBT Technology
- Low Switching Losses
- 5µs SCSOA
- Square RBSOA
- 100% of The Parts Tested for I_{LM} ①
- Positive $V_{CE\ (on)}$ Temperature Coefficient.
- Ultra Fast Soft Recovery Co-pak Diode
- Tighter Distribution of Parameters
- Lead-Free, RoHS Compliant

Benefits

- High Efficiency in a Wide Range of Applications
- Suitable for a Wide Range of Switching Frequencies due to Low $V_{CE\ (ON)}$ and Low Switching Losses
- Rugged Transient Performance for Increased Reliability
- Excellent Current Sharing in Parallel Operation
- Low EMI



Super-247

G	C	E
Gate	Collector	Emitter

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	240⑤	
I_C @ T_C = 100°C	Continuous Collector Current	160⑤	
$I_{NOMINAL}$	Nominal Current	120	
I_{CM}	Pulse Collector Current, V_{GE} = 15V	360	
I_{LM}	Clamped Inductive Load Current, V_{GE} = 20V ①	480	A
I_F @ T_C = 25°C	Diode Continous Forward Current	240	
I_F @ T_C = 100°C	Diode Continous Forward Current	160	
I_{FM}	Diode Maximum Forward Current ②	480	
V_{GE}	Continuous Gate-to-Emitter Voltage	±20	V
	Transient Gate-to-Emitter Voltage	±30	
P_D @ T_C = 25°C	Maximum Power Dissipation	750	W
P_D @ T_C = 100°C	Maximum Power Dissipation	375	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case-(each IGBT) ④	–––	–––	0.20	
$R_{\theta JC}$ (Diode)	Thermal Resistance Junction-to-Case-(each Diode) ④	–––	–––	0.63	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	–––	0.24	–––	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (typical socket mount)	–––	–––	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 100µA ③
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.27	—	V/°C	V_{GE} = 0V, I_C = 4.0mA (25°C-175°C)
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	1.70	2.05	V	I_C = 120A, V_{GE} = 15V, T_J = 25°C
		—	2.15	—		I_C = 120A, V_{GE} = 15V, T_J = 150°C
		—	2.20	—		I_C = 120A, V_{GE} = 15V, T_J = 175°C
$V_{GE(th)}$	Gate Threshold Voltage	4.0	—	6.5	V	V_{CE} = V_{GE}, I_C = 5.6mA
$\Delta V_{GE(th)}/\Delta TJ$	Threshold Voltage temp. coefficient	—	-17	—	mV/°C	V_{CE} = V_{GE}, I_C = 5.6mA (25°C - 175°C)
gfe	Forward Transconductance	—	77	—	S	V_{CE} = 50V, I_C = 120A
I_{CES}	Collector-to-Emitter Leakage Current	—	1.0	150	µA	V_{GE} = 0V, V_{CE} = 600V
		—	2.3	—	mA	V_{GE} = 0V, V_{CE} = 600V, T_J = 175°C
V_{FM}	Diode Forward Voltage Drop	—	2.4	3.0	V	I_F = 120A
		—	1.9	—		I_F = 120A, T_J = 175°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±400	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.⑥	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	240	360	nC	I_C = 120A
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	70	105		V_{GE} = 15V
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	90	135		V_{CC} = 400V
E_{on}	Turn-On Switching Loss	—	5750	7990	µJ	I_C = 120A, V_{CC} = 400V, V_{GE} = 15V
E_{off}	Turn-Off Switching Loss	—	3430	4360		R_G = 4.7Ω, L = 66µH, T_J = 25°C
E_{total}	Total Switching Loss	—	9180	12350		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	80	100	ns	I_C = 120A, V_{CC} = 400V, V_{GE} = 15V
t_r	Rise time	—	70	125		R_G = 4.7Ω, L = 66µH, TJ = 25°C
$t_{d(off)}$	Turn-Off delay time	—	190	220		
t_f	Fall time	—	40	60		
E_{on}	Turn-On Switching Loss	—	7740	—	µJ	I_C = 120A, V_{CC} = 400V, V_{GE}=15V
E_{off}	Turn-Off Switching Loss	—	4390	—		R_G=4.7Ω, L=66µH, T_J = 175°C
E_{total}	Total Switching Loss	—	12130	—		Energy losses include tail & diode reverse recovery
$t_{d(on)}$	Turn-On delay time	—	80	—	ns	I_C = 120A, V_{CC} = 400V, V_{GE} = 15V
t_r	Rise time	—	75	—		R_G = 4.7Ω, L = 66µH
$t_{d(off)}$	Turn-Off delay time	—	230	—		T_J = 175°C
t_f	Fall time	—	55	—		
C_{ies}	Input Capacitance	—	7750	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	550	—		V_{CC} = 30V
C_{res}	Reverse Transfer Capacitance	—	225	—		f = 1.0Mhz
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 175°C, I_C = 480A V_{CC} = 480V, Vp =600V Rg = 4.7Ω, V_{GE} = +20V to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	µs	V_{CC} = 400V, Vp =600V Rg = 4.7Ω, V_{GE} = +15V to 0V
Erec	Reverse Recovery Energy of the Diode	—	500	—	µJ	T_J = 175°C
t_{rr}	Diode Reverse Recovery Time	—	130	—	ns	V_{CC} = 400V, I_F = 120A
I_{rr}	Peak Reverse Recovery Current	—	36	—	A	V_{GE} = 15V, Rg = 4.7Ω, L =100µH

Notes:

① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 66µH, R_G = 4.7Ω, tested in production $I_{LM} \leq$ 400A.
② Pulse width limited by max. junction temperature.
③ Refer to AN-1086 for guidelines for measuring $V_{(BR)CES}$ safely.
④ R_θ is measured at T_J of approximately 90°C.
⑤ Calculated continuous current based on maximum allowable junction temperature. Package IGBT current limit is 195A. Package diode current limit is 120A. Note that current limitations arising from heating of the device leads may occur.
⑥ Maximum limits are based on statistical sample size characterization.

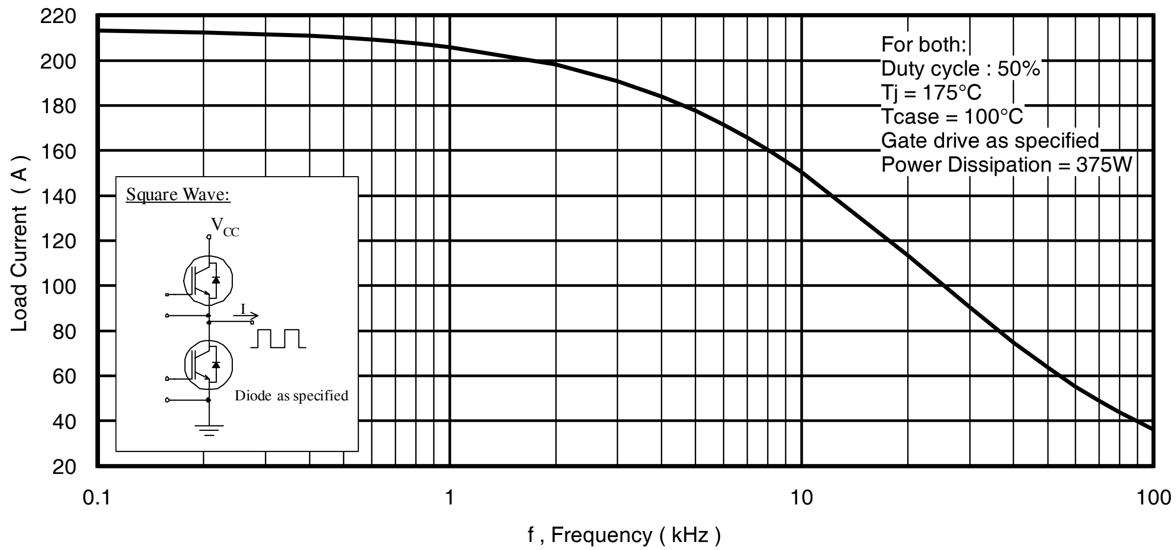


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

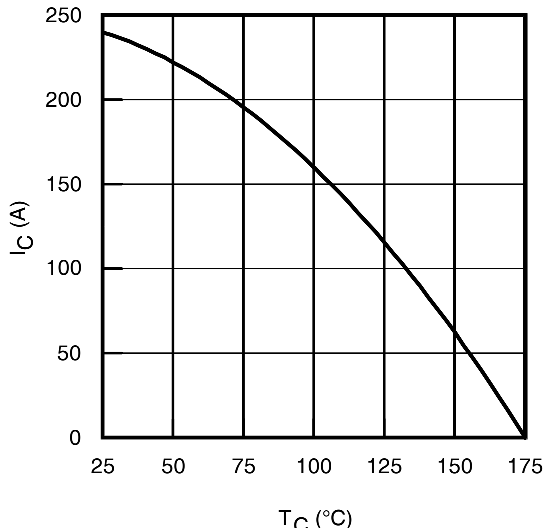


Fig. 2 - Maximum DC Collector Current vs. Case Temperature

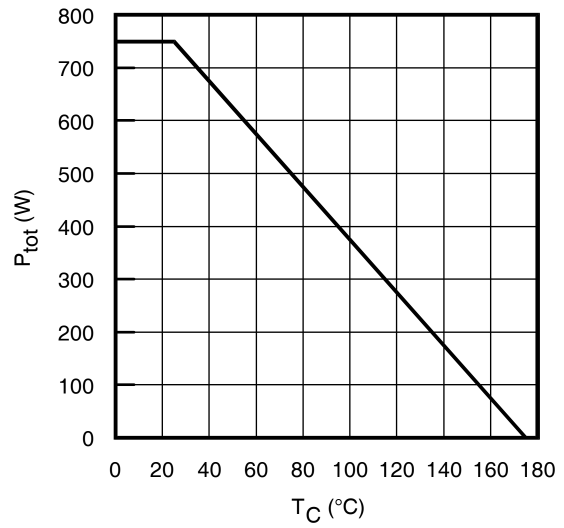


Fig. 3 - Power Dissipation vs. Case Temperature

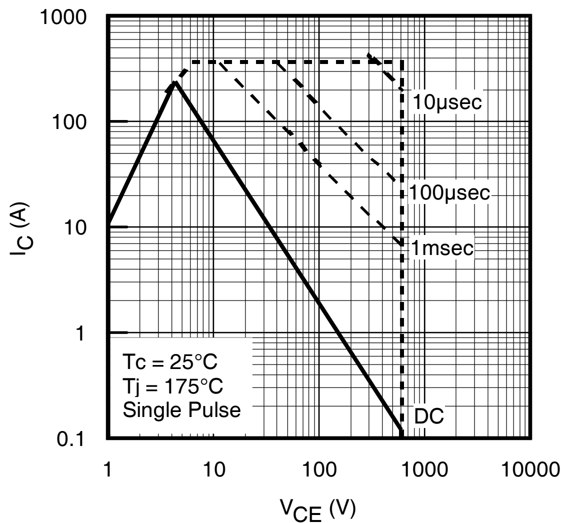


Fig. 4 - Forward SOA
T_C = 25°C, $T_J \leq$ 175°C; V_{GE} =15V

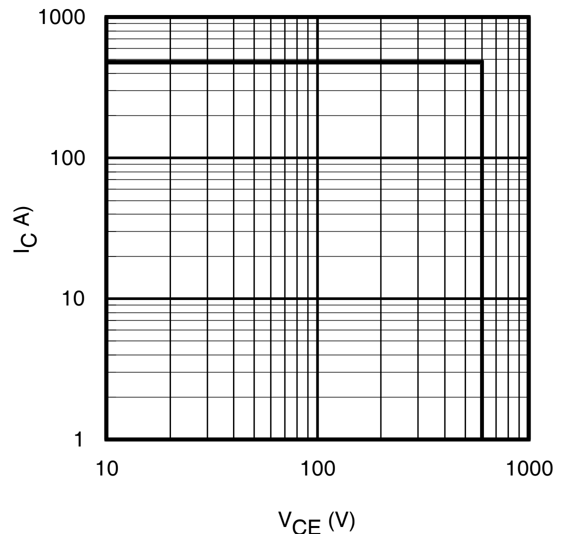


Fig. 5 - Reverse Bias SOA
T_J = 175°C; V_{GE} =20V

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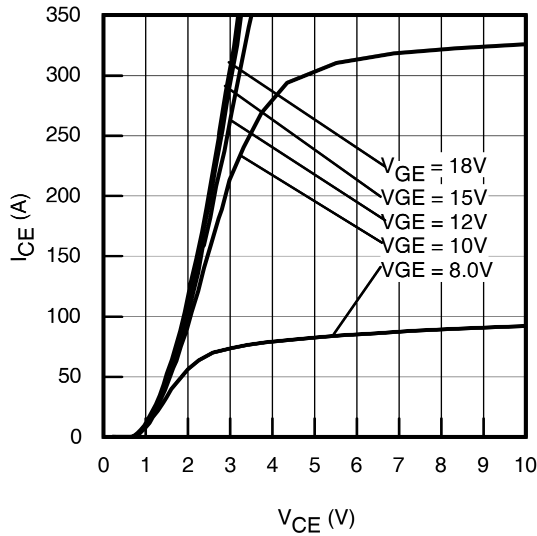

Fig. 6 - Typ. IGBT Output Characteristics
T_J = -40°C; tp = 80µs

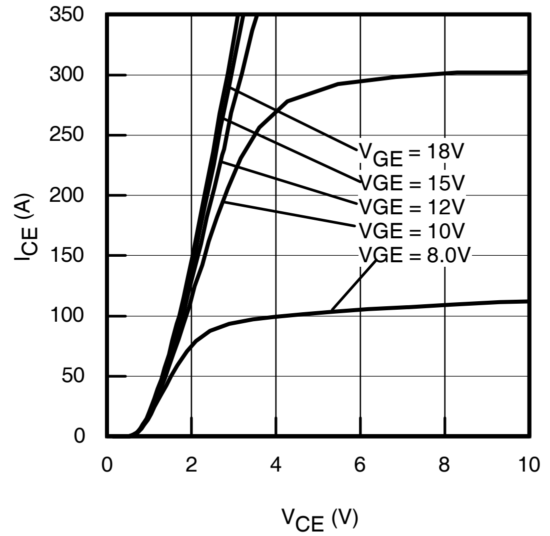

Fig. 7 - Typ. IGBT Output Characteristics
T_J = 25°C; tp = 80µs

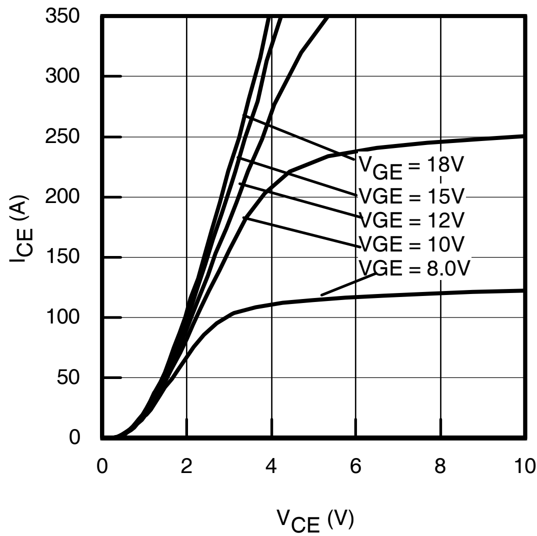

Fig. 8 - Typ. IGBT Output Characteristics
T_J = 175°C; tp = 80µs

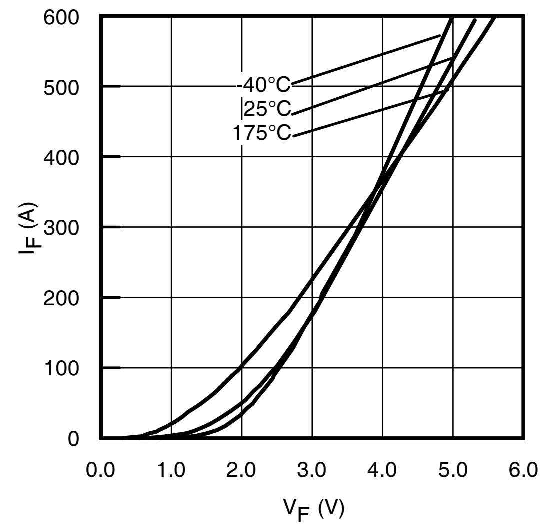

Fig. 9 - Typ. Diode Forward Characteristics
tp = 80µs

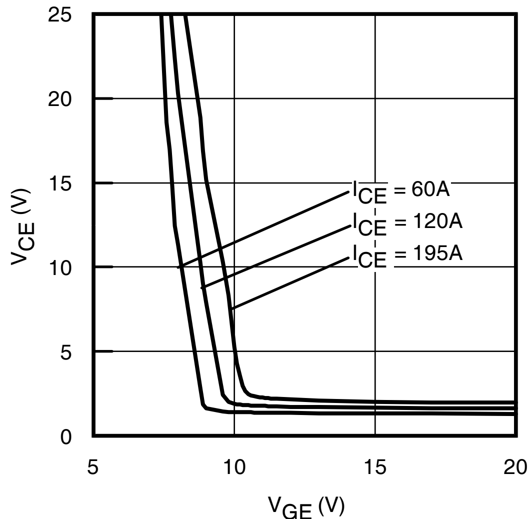

Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = -40°C

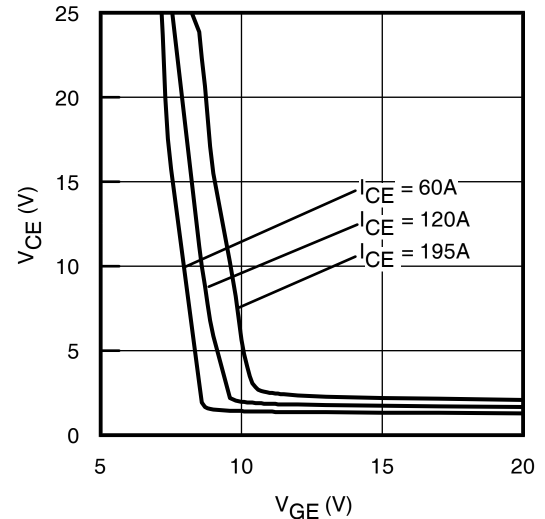

Fig. 11 - Typical V_{CE} vs. V_{GE}
T_J = 25°C

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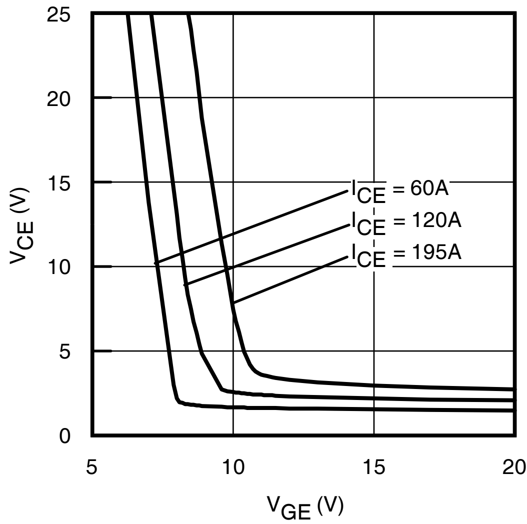


Fig. 12 - Typical V_{CE} vs. V_{GE}
T_J = 175°C

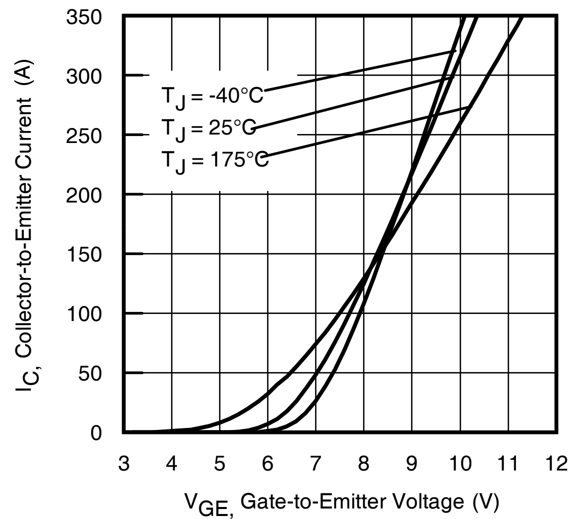


Fig. 13 - Typ. Transfer Characteristics
V_{CE} = 50V; tp = 10µs

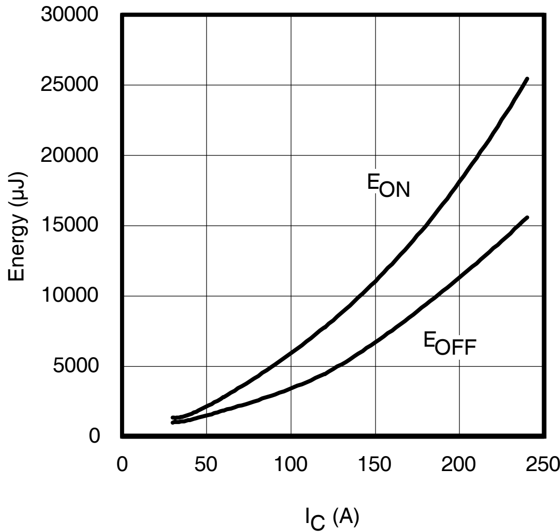


Fig. 14 - Typ. Energy Loss vs. I_C
T_J = 175°C; L = 66µH; V_{CE} = 400V, R_G = 4.7Ω; V_{GE} = 15V

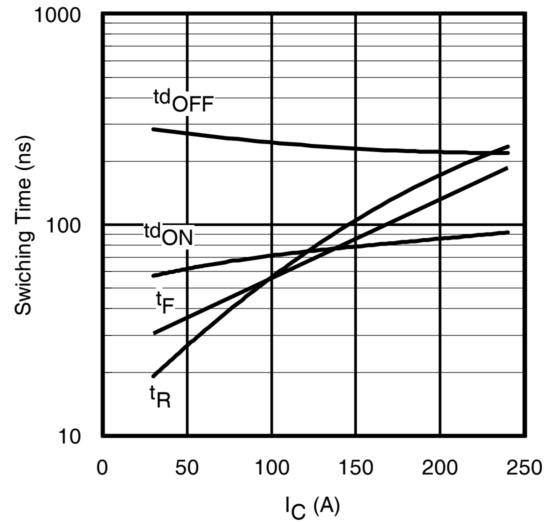


Fig. 15 - Typ. Switching Time vs. I_C
T_J = 175°C; L = 66µH; V_{CE} = 400V, R_G = 4.7Ω; V_{GE} = 15V

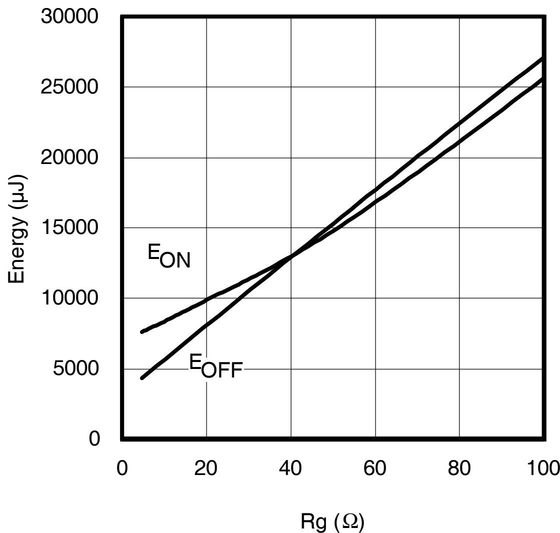


Fig. 16 - Typ. Energy Loss vs. R_G
T_J = 175°C; L = 66µH; V_{CE} = 400V, I_{CE} = 120A; V_{GE} = 15V

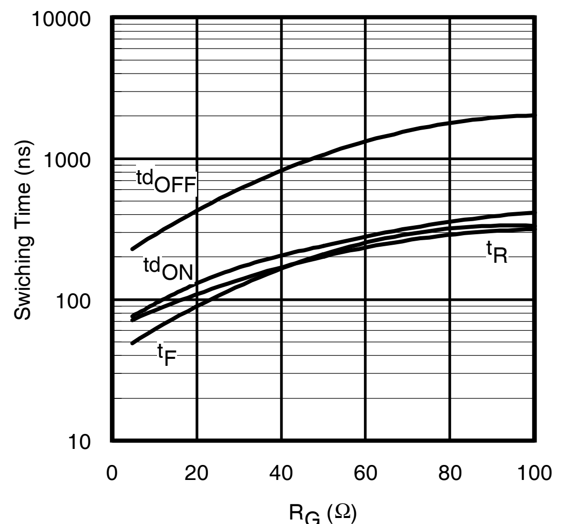


Fig. 17 - Typ. Switching Time vs. R_G
T_J = 175°C; L = 66µH; V_{CE} = 400V, I_{CE} = 120A; V_{GE} = 15V

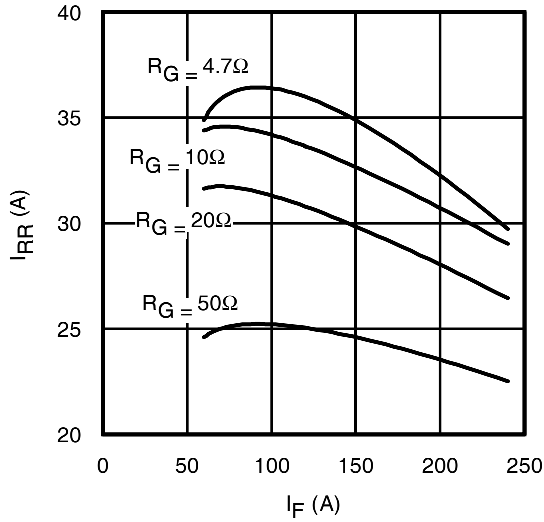


Fig. 18 - Typ. Diode I_{RR} vs. I_F
T_J = 175°C

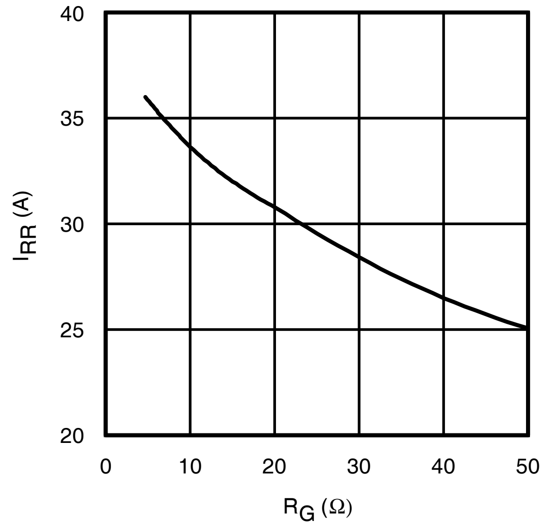


Fig. 19 - Typ. Diode I_{RR} vs. R_G
T_J = 175°C

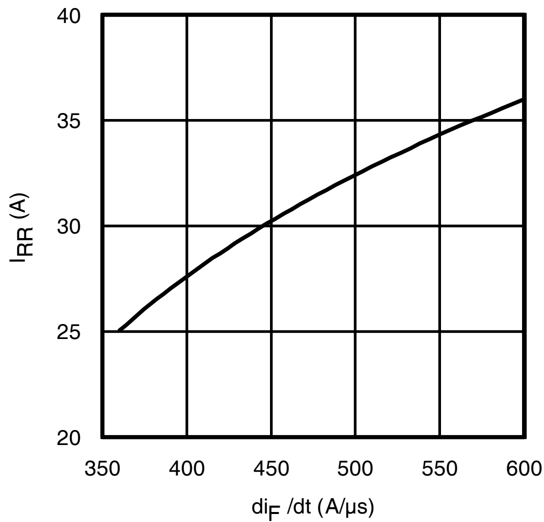


Fig. 20 - Typ. Diode I_{RR} vs. di_F/dt
V_{CC} = 400V; V_{GE} = 15V; I_F = 120A; T_J = 175°C

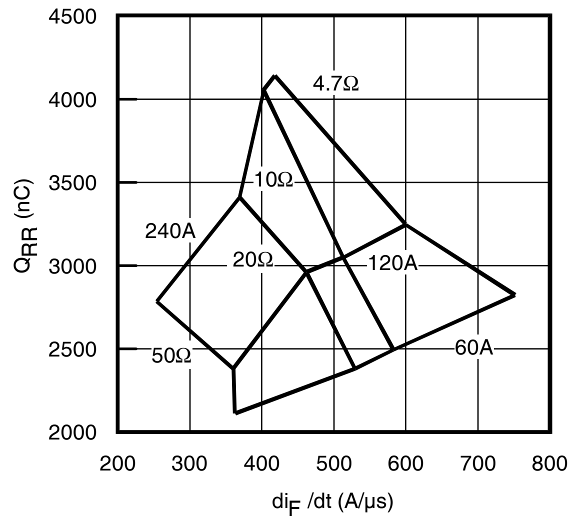


Fig. 21 - Typ. Diode Q_{RR} vs. di_F/dt
V_{CC} = 400V; V_{GE} = 15V; T_J = 175°C

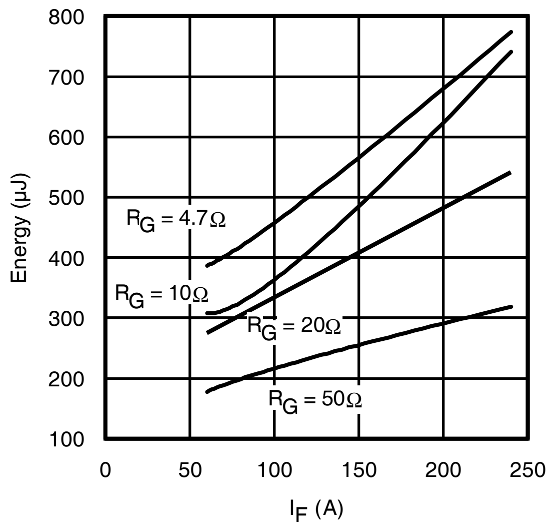


Fig. 22 - Typ. Diode E_{RR} vs. I_F
T_J = 175°C

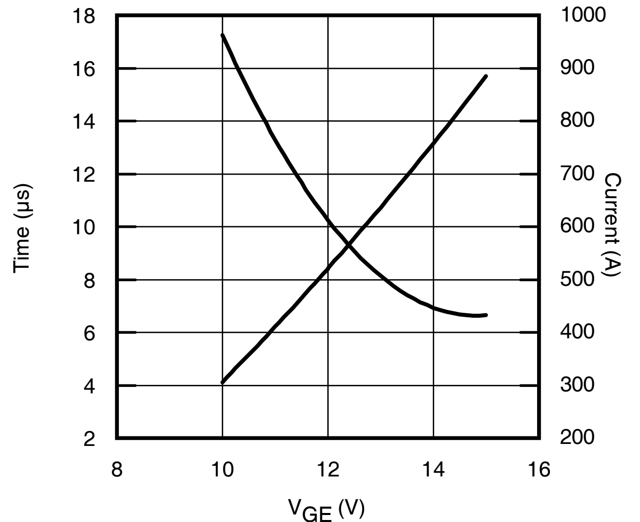


Fig. 23 - V_{GE} vs. Short Circuit Time
V_{CC} = 400V; T_C = 25°C

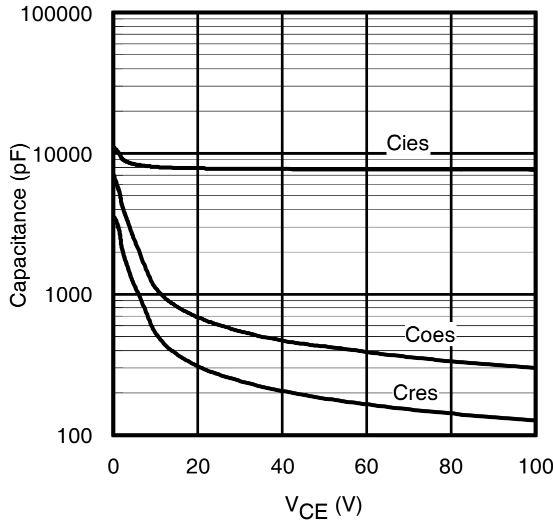


Fig. 24 - Typ. Capacitance vs. V_{CE}
V_{GE}= 0V; f = 1MHz

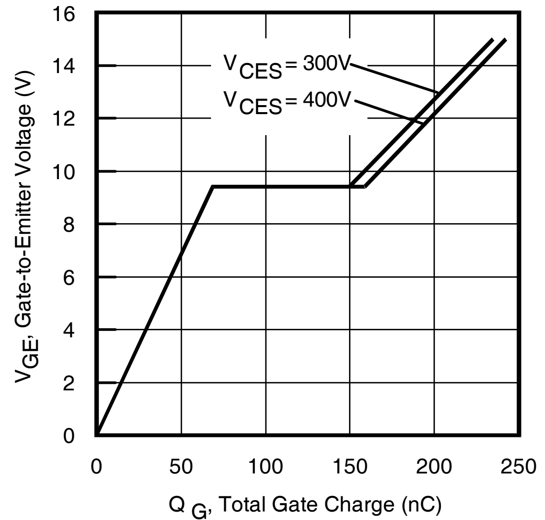
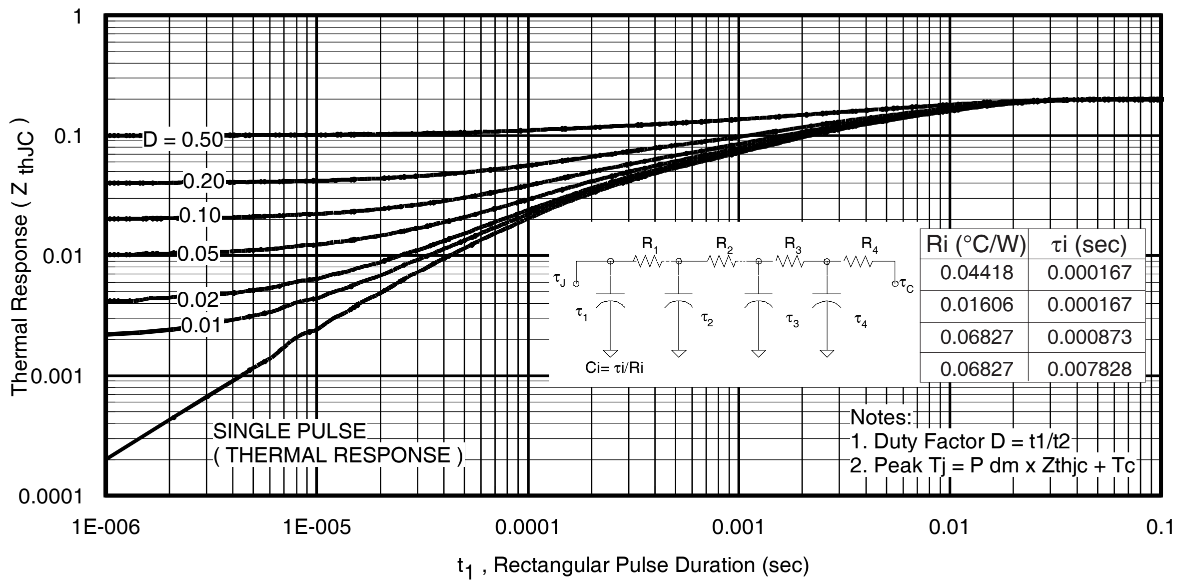
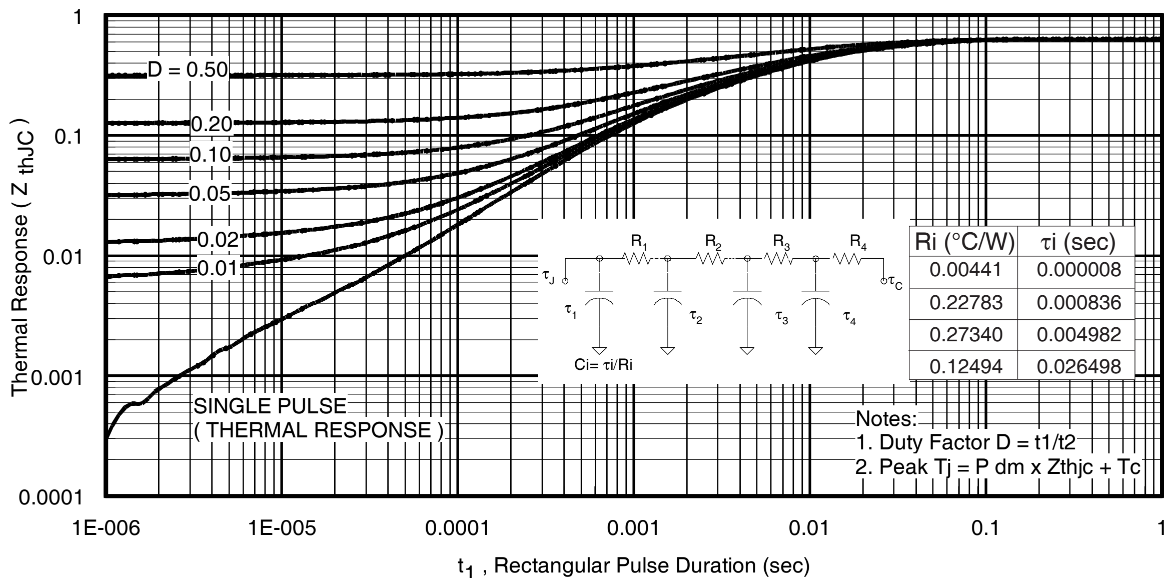


Fig. 25 - Typical Gate Charge vs. V_{GE}
I_{CE} = 120A; L = 100µH



Ri (°C/W)	τi (sec)
0.04418	0.000167
0.01606	0.000167
0.06827	0.000873
0.06827	0.007828

Fig 26. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)



Ri (°C/W)	τi (sec)
0.00441	0.000008
0.22783	0.000836
0.27340	0.004982
0.12494	0.026498

Fig. 27. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)

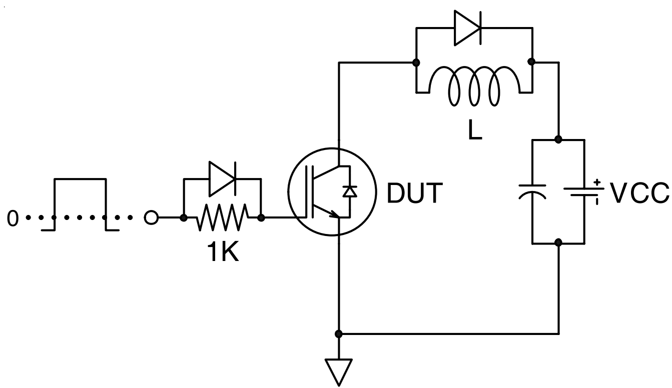


Fig.C.T.1 - Gate Charge Circuit (turn-off)

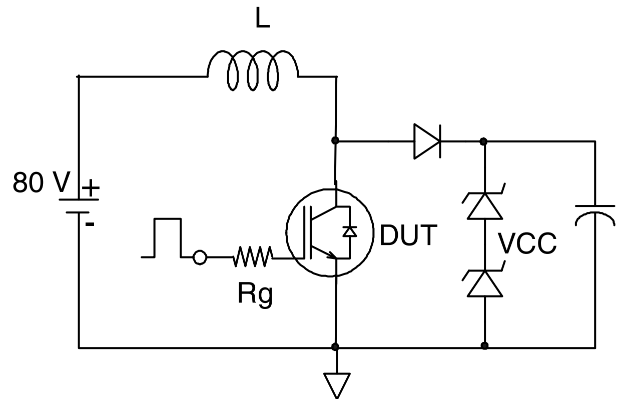
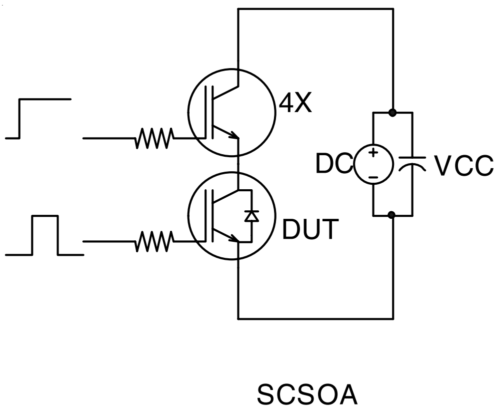


Fig.C.T.2 - RBSOA Circuit



SCSOA

Fig.C.T.3 - S.C. SOA Circuit

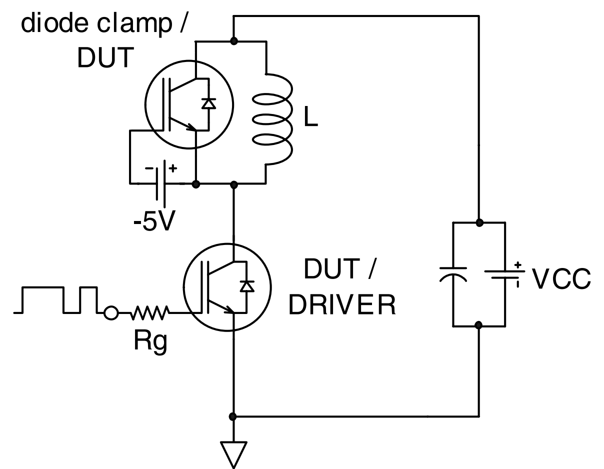


Fig.C.T.4 - Switching Loss Circuit

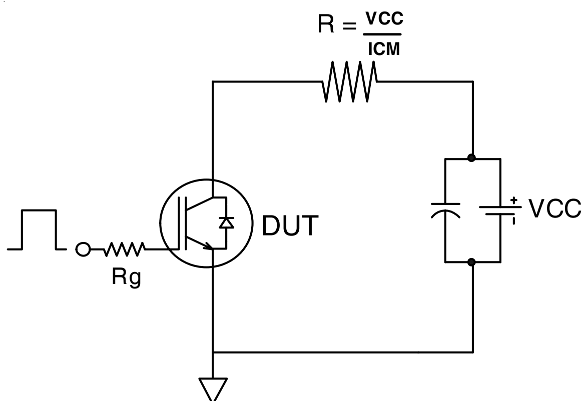


Fig.C.T.5 - Resistive Load Circuit

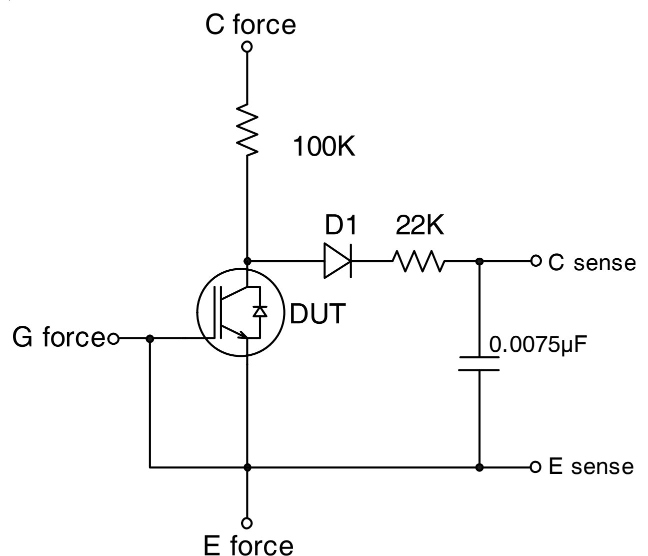


Fig.C.T.6 - BVCES Filter Circuit

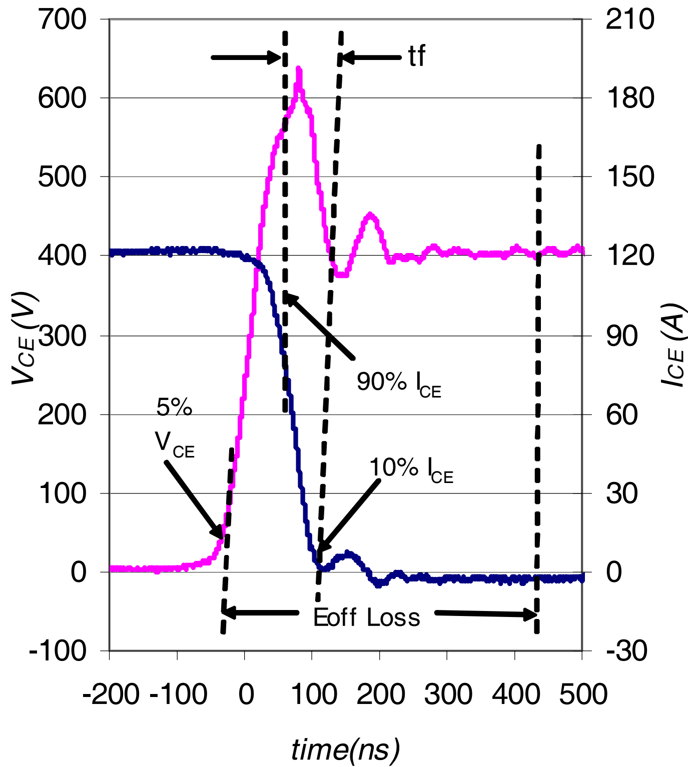


Fig. WF1 - Typ. Turn-off Loss Waveform
@ T_J = 175°C using Fig. CT.4

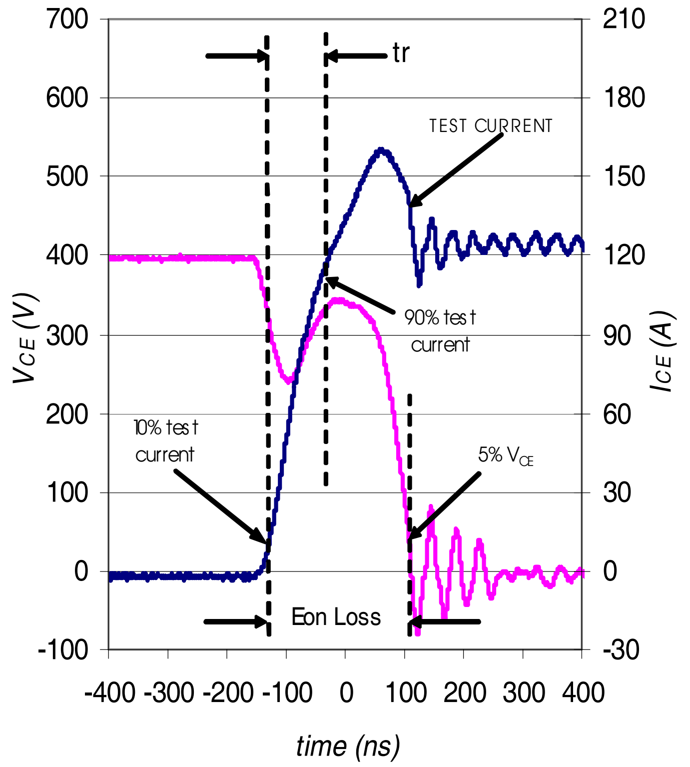


Fig. WF2 - Typ. Turn-on Loss Waveform
@ T_J = 175°C using Fig. CT.4

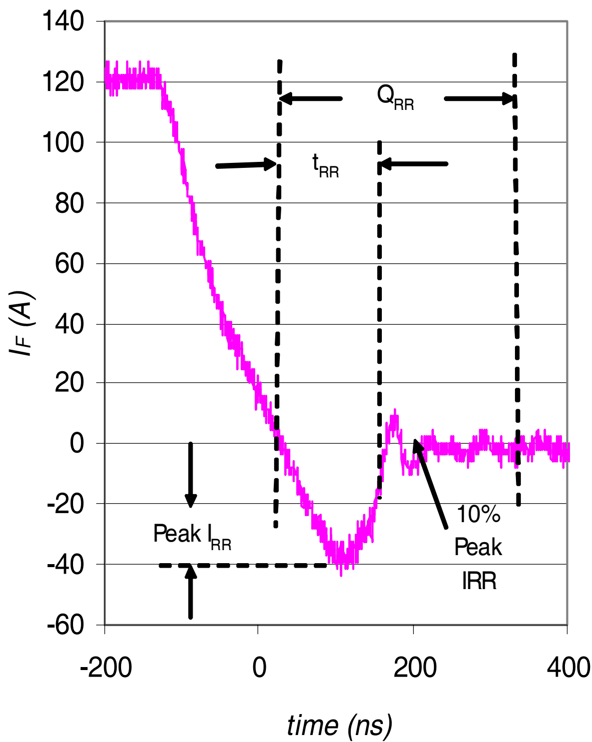


Fig. WF3 - Typ. Diode Recovery Waveform
@ T_J = 175°C using Fig. CT.4

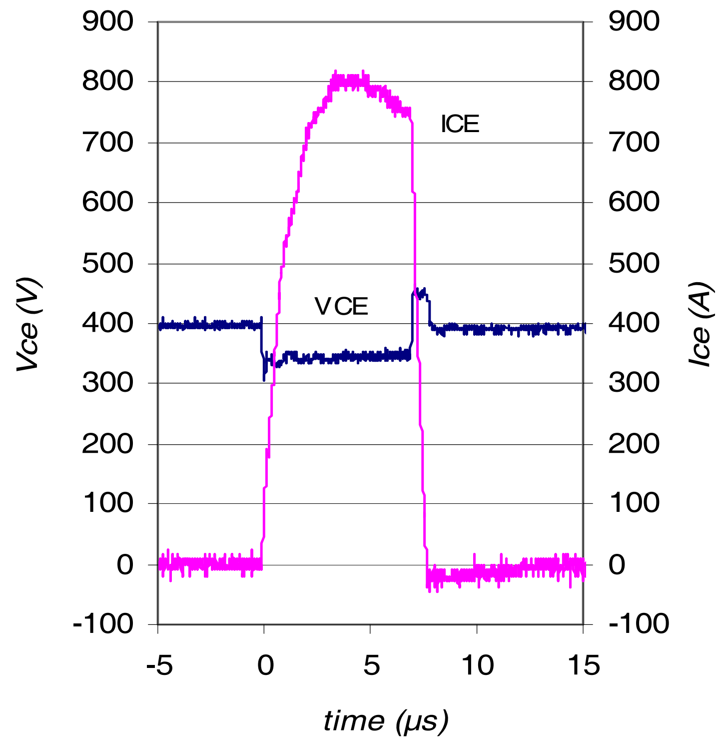


Fig. WF4 - Typ. S.C. Waveform
@ T_J = 25°C using Fig. CT.3

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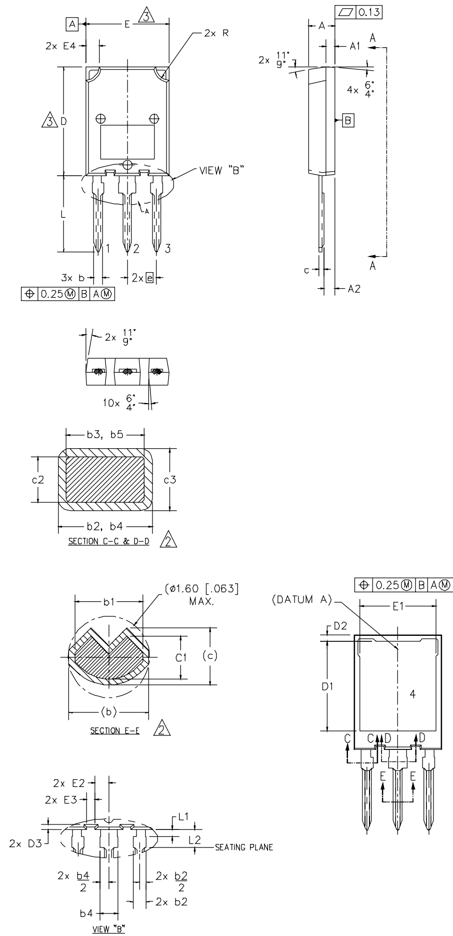
Case Outline and Dimensions — Super-247



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
2. DIMENSIONS b1, b3, b5, c1 & c3 APPLY TO BASE METAL ONLY.
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER EXTREMES OF THE PLASTIC BODY.
4. ALL DIMENSIONS SHOWN IN MILLIMETERS.
5. CONTROLLING DIMENSION: MILLIMETER.
6. OUTLINE CONFORMS TO JEDEC OUTLINE TO-274AA

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.50	5.50	.177	.217	
A1	1.45	2.15	.057	.085	
A2	1.65	2.35	.065	.093	
b	1.45	1.60	.054	.063	
b1	1.40	1.50	.055	.059	2
b2	2.00	2.40	.079	.094	
b3	1.95	2.35	.077	.093	2
b4	3.00	3.15	.118	.124	
b5	2.95	3.35	.116	.132	2
c	1.10	1.30	.043	.051	
c1	0.90	1.10	.035	.043	2
c2	0.65	0.85	.026	.033	
c3	0.50	0.70	.020	.028	2
D	19.80	20.80	.780	.819	3
D1	15.50	16.10	.610	.634	
D2	0.70	1.30	.028	.051	
D3	0.75	1.25	.030	.049	
E	15.10	16.10	.594	.634	3
E1	13.30	13.90	.524	.547	
E2	2.25	2.70	.089	.109	
E3	1.20	1.70	.047	.067	
E4	2.00	3.00	.079	.118	
e	5.45 BSC		.215 BSC		
L	13.80	14.80	.535	.583	
L1	1.00	1.60	.039	.063	
L2	3.85	4.25	.152	.167	
R	2.00	3.00	.079	.118	

LEAD ASSIGNMENTS

MOSFET

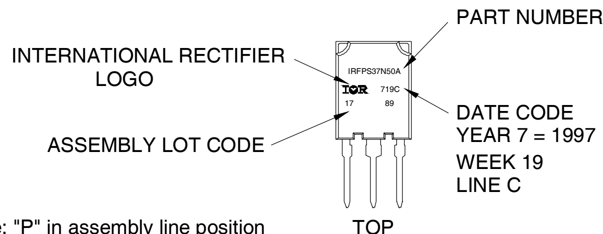
1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

IGBT

1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

Super-247 (TO-274AA) Part Marking Information

EXAMPLE: THIS IS AN IRFPS37N50A WITH
ASSEMBLY LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



Note: "P" in assembly line position indicates "Lead-Free"

TOP

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

International
IGR Rectifier

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA
To contact International Rectifier, please visit http://www.irf.com/whoto-call/

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